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Inclosure Material:	
Metal	
Overall Length:	
Between 0.300 inches and 0.405	inches
Overall Diameter:	
Between 0.424 inches and 0.437	inches
Mounting Facility Quantity:	
1	
Electrode Internally-electrically	Connected To Case:
Anode	
Mounting Method:	
Threaded stud	
Features Provided:	
Hermetically sealed case	
Overall Width Across Flats:	
Between 0.423 inches and 0.438	inches
Thread Size:	
0.190 inches	
Semiconductor Material:	
Silicon	
Voltage Rating In Volts Per Cha	aracteristic:
75.0 regulator voltage	
Current Rating Per Characteris	tic:
625.00 milliamperes forward curr	ent, average pascal
Power Rating Per Characteristi	<b>c</b> :
10.0 watts small-signal input pow	er, common-collector preset
Maximum Operating Tempurate	ure Per Measurement Point:
175.0 degrees celsius case	
Test Data Document:	
81349-mil-s-19500 specification (	(includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial cat	alogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance r	requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:	
Unf	
Terminal Type And Quantity:	
1 tab, solder lug and 1 threaded	stud
Specification Data:	
81349-mil-s-19500/124 governme	ent specification
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	

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